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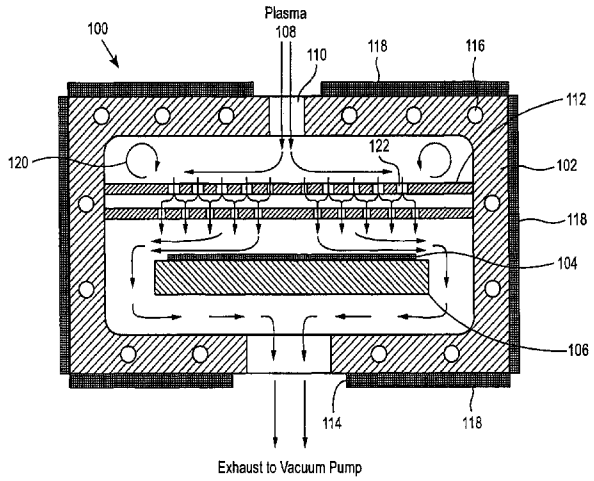
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(54) **Title:** HIGH CHAMBER TEMPERATURE PROCESS AND CHAMBER DESIGN FOR PHOTO-RESIST STRIPPING AND POST-METAL ETCH PASSIVATION



(57) **Abstract:** A vacuum chamber for passivation and/or stripping a photoresist layer formed on a semiconductor substrate. The chamber includes an internal chamber body that forms a cavity to surround the substrate and has a plurality of gas passages extending therethrough to the cavity and one or more heaters to heat the internal chamber body. The internal chamber body is slidably mounted on an external chamber body that surrounds a side of the internal chamber with a gap therebetween. The device also includes: an exhaust unit operative to pump the gas from the cavity; a chamber top mounted on the internal chamber body to cover a top surface of the internal chamber body with a gap therebetween and having an opening in fluid communication with the gas passages; and a plasma source operative to energize the gas into a plasma state and coupled to the opening for fluid communication with the cavity.

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